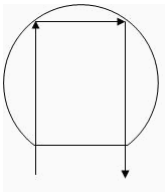
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Secondary Flat Length	none / 18.5mm +/-2.5mm	Wafer Vendor
	6.0	Overall Thickness	399.00 +/- 6.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00um	ADE 100% to ASTM F534
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	390.00 +/- 5.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Any	Wafer Vendor
	17.0	Handle Resistivity	0.01 ~ 0.02 Ohm-cm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and lasermark.	Wafer Vendor
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and / or device Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	8.00 +/- 1.00 µm	ADE Single Point . 100%
	25.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	0.001 ~ 0.002 Ohm-cm	Wafer Vendor
	29.0	Voids	none	Wafer Vendor
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

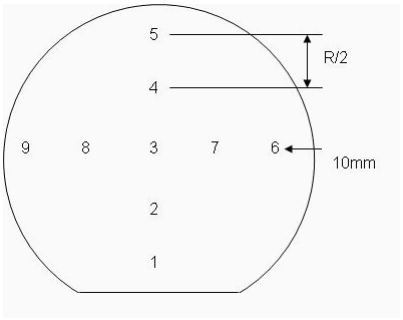
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information